

# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	$V_{DSS}$	-60	V		
Gate-Source Voltage	$V_{GSS}$	±20	V		
Continuous Drain Current (Note 6) V <sub>GS</sub> = -10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +100°C	I <sub>D</sub>	-6.3 -4.4	А
Continuous Drain Current (Note 7) V <sub>GS</sub> = -10V	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I <sub>D</sub>	-26 -18	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	-40	Α		
Maximum Continuous Body Diode Forward Current (Note 6)			IS	-2.0	Α
Avalanche Current (Note 8) L = 0.1mH	I <sub>AS</sub>	-21	Α		
Avalanche Energy (Note 8) L = 0.1mH			E <sub>AS</sub>	30	mJ

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.5	W
Thormal Posistance Junction to Ambient (Note 5)	Steady state	D.	100	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{ heta JA}$	53	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	2.8	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	D	52	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	27	
Thermal Resistance, Junction to Case (Note 7)	$R_{ heta JC}$	2.9		
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

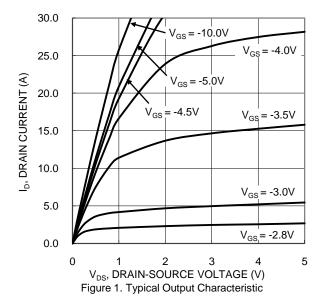
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

0			_			T 10 10	
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-60	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	_	_	-1	μΑ	$V_{DS} = -60V$ , $V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_		±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.0	_	-3.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	В		36 48	48	m()	$V_{GS} = -10V, I_D = -5A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	44	60		$V_{GS} = -4.5V$ , $I_{D} = -4A$	
Diode Forward Voltage	$V_{SD}$	_	-0.7	-1.2	V	$V_{GS} = 0V$ , $I_S = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C <sub>iss</sub>	_	1525	_	рF		
Output Capacitance	Coss	_	90	_	рF	$V_{DS} = -30V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	70	_	pF		
Gate Resistance	$R_g$	_	16	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = -4.5V)	$Q_g$	_	14.5	_	nC	V <sub>DS</sub> = -30V, I <sub>D</sub> = -5A	
Total Gate Charge (V <sub>GS</sub> = -10V)	Qg	_	30.6	_	nC		
Gate-Source Charge	$Q_{gs}$	_	4.9	_	nC		
Gate-Drain Charge	$Q_{gd}$	_	5.2	_	nC		
Turn-On Delay Time	t <sub>D(ON)</sub>	_	5.3	_	ns	V <sub>GS</sub> = -10V, V <sub>DS</sub> = -30V,	
Turn-On Rise Time	t <sub>R</sub>	_	15.4	_	ns		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	79.2	_	ns	$R_G = 3\Omega$ , $I_D = -5A$	
Turn-Off Fall Time	t <sub>F</sub>	_	45.3	_	ns	1	
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	15.2	_	ns	I <sub>F</sub> = -5A, di/dt = -100A/μs	
Body Diode Reverse Recovery Charge	$Q_{RR}$	_	9.3	_	nC	$I_F = -5A$ , di/dt = -100A/ $\mu$ s	

Notes:

- $5. \ \, \text{Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided}.$
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J$  = +25°C.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.





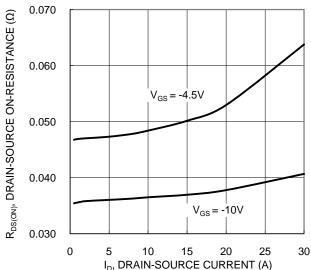


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

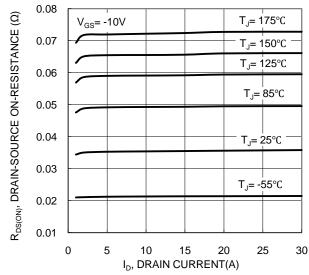


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

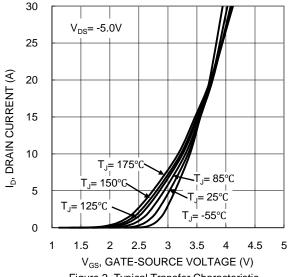
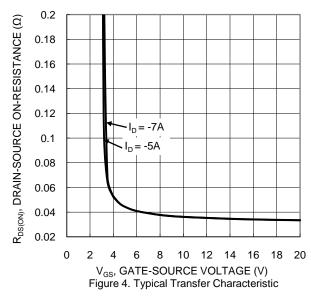


Figure 2. Typical Transfer Characteristic



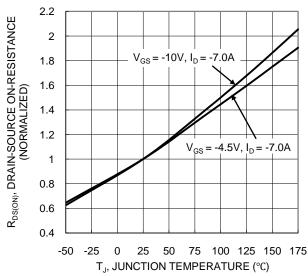


Figure 6. On-Resistance Variation with Temperature



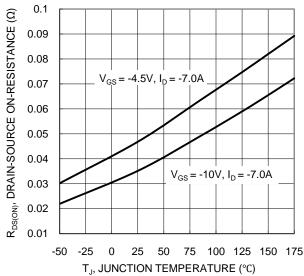
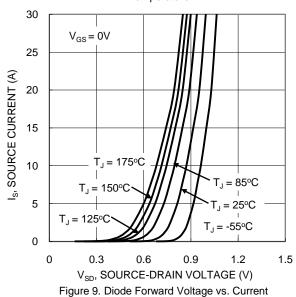


Figure 7. On-Resistance Variation with Temperature



10 8 6  $V_{DS} = -30V, I_{D} = -5A$  $V_{GS}(V)$ 4 2 0 0 4 8 12 16 20 24 28 32

Qg (nC) Figure 11. Gate Charge

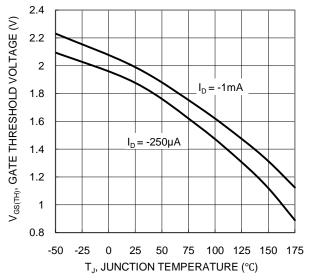
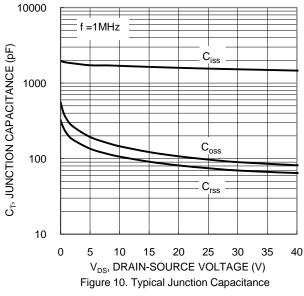
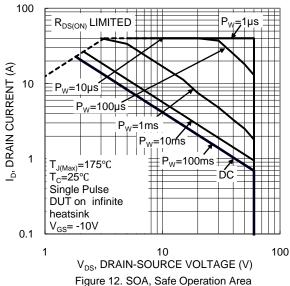


Figure 8. Gate Threshold Variation vs Temperature





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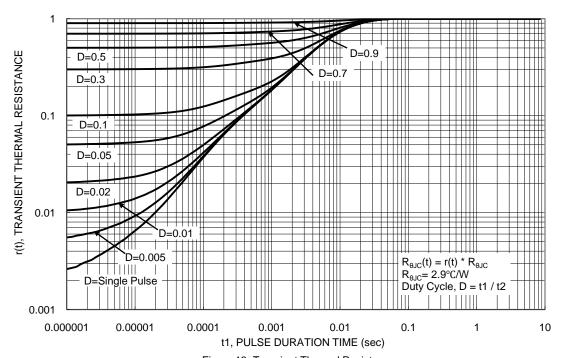


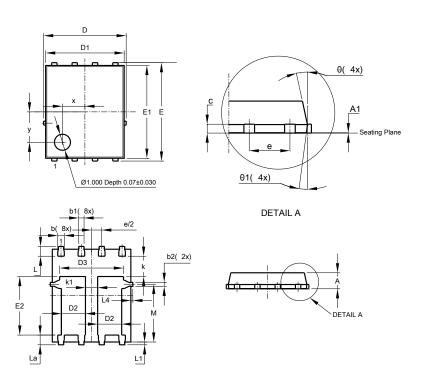
Figure 13. Transient Thermal Resistance



### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI5060-8 (Type C)

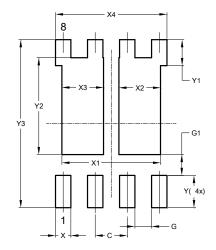


PowerDI5060-8 (Type C)					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0	0.05	0.02		
b	0.33	0.51	0.41		
b1	0.300	0.366	0.333		
b2	0.20	0.35	0.25		
С	0.23	0.33	0.277		
D	5.15 BSC				
D1	4.85	4.95	4.90		
D2	1.40	1.60	1.50		
D3	-	-	3.98		
Е	6.15 BSC				
E1	5.75	5.85	5.80		
E2	3.56	3.76	3.66		
е	1.27BSC				
k	1	-	1.27		
k1	0.56	-	-		
L	0.51	0.71	0.61		
La	0.51	0.71	0.61		
L1	0.05	0.20	0.175		
L4	-	-	0.125		
М	3.50	3.71	3.605		
х	-	-	1.400		
У	-	-	1.900		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI5060-8 (Type C)



Dimensions	Value			
	(in mm)			
С	1.270			
G	0.660			
G1	0.820			
Х	0.610			
X1	3.910			
X2	1.650			
Х3	1.650			
X4	4.420			
Υ	1.270			
Y1	1.020			
Y2	3.810			
Y3	6.610			



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